Amendments to the Specification:

Please replace the paragraph beginning at page 5, line 6, with the following amended paragraph:

-- Paragraphs [0004] and [0005] of Japanese Patent Laid-Open Publication No. 282651/2003 ~~JP '651~~ (JP '651) ~~discloses~~ disclose that a metal layer 1 made of an alloy of copper and a metal other than copper is provided on a surface of a flexible insulating film 2 in order to ensure adhesion strength between the flexible insulating film and a wiring pattern, then on a surface of the metal layer 1 a copper foil is arranged to form a composite, and from the composite a flexible wiring board is produced. JP '651 further describes that at the peripheral lower part of the lead of the wiring pattern formed by the use of such a composite, the metal layer 1 remains as an unremoved part as shown in Fig. 5 of JP '651, and further discloses that because of the unremoved part, abnormal deposition 6 of the plating metal takes place. Moreover, JP '651 further discloses that at the place of the abnormal deposition 6 of the plating metal, a crystal of tin grows and becomes a "whisker", and because of the whisker, a short-circuit takes place in the wiring pattern. That is to say, if the metal layer 1 provided to ensure adhesion strength of the wiring pattern is left as it is and if a tin plating layer is formed on the surface of the metal layer 1, a whisker is generated from the thus formed tin plating layer. In JP '651, therefore, the metal layer 1 is completely removed as described in paragraph [0023] thereof. --

Please replace the paragraph beginning at page 12, line 15, with the following amended paragraph:

-- Fig. 5 is a sectional view of a wiring pattern formed by removing a base metal layer and then performing ~~microethcing~~ microetching; --

Please replace the paragraph beginning at page 12, line 18, with the following amended paragraph:

-- Fig. 6 is a sectional view of a wiring pattern formed by removing a base metal layer and then performing ~~microethcing~~ microetching; --

Please replace the paragraph beginning at page 12, line 23, with the following amended paragraph:

-- Fig. 8 ~~is an~~ is a perspective drawing of the SEM photograph of Fig. 7. --

Please replace the paragraph beginning at page 16, line 21, with the following amended paragraph:

-- In the present invention, after formation of the base metal layer 13 and before formation of the conductive metal layer 20 on the surface of the base metal layer 13, a sputtering copper layer 15 can be formed in the same manner as in the formation of the base metal layer 13 using the same metal as that of the conductive metal layer (e.g., copper layer) to be directly formed on the surface of the base metal layer 13, as shown in Fig. 1(c). For example, in the case where the base metal layer 13 is formed by sputtering using nickel and chromium, a copper layer 15 is formed by sputtering as a part of a conductive metal layer 20 to be formed on the surface of the base metal layer 13, and on the thus formed sputtering copper layer 15, a layer 17, the other part of the conductive metal layer 20 is further formed. The thickness of the sputtering copper layer 15 is in the ~~rage~~ range of usually 10 to 2000 nm, preferably 20 to 500 nm. The ratio between the average thickness of the base metal layer 13 and the thickness of the sputtering copper layer 15 is in the range of usually 1:20 to 1:100, preferably 1:25 to 1:60. --

Please replace the paragraph beginning at page 21, line 5, with the following amended paragraph:

-- For the ~~microethcing~~ microetching, an etching solution usually used is employable, and for example, a potassium persulfate ($K_2S_2O_8$) solution, a HCl solution or the aforesaid etching solution used for forming the wiring pattern is employable. If the contact time with the etching solution is long, copper that is a wiring pattern-forming conductive metal is dissolved in a large amount and the wiring pattern itself is thinned, so that the contact time of the wiring pattern with the etching solution in the microetching is in the range of usually 2 to 60 seconds, preferably about 10 to 45 seconds at the solution temperature of 20 to 60°C. --

Please replace the paragraph beginning at page 26, line 16, with the following amended paragraph:

-- The printed wiring board of the invention is produced as follows. Onto the base metal layer which is formed on the insulating film by sputtering or the like, the conductive metal layer (e.g., a copper layer formed by plating or a ~~deposite~~ deposit of a sputtering copper layer and a plating copper layer provided thereon) which is made of a metal having different properties from the metal of the base metal layer is laminated; then the conductive metal layer thus laminated is selectively etched to form a wiring pattern composed of the conductive metal layer; then microetching is carried out to mainly treat the surface of the conductive metal layer; and the base metal layer is further treated with a treating liquid capable of dissolving and/or passivating the metal that forms the base metal layer, to dissolve and remove most of the metal that forms the base metal layer exposed between the wiring patterns and to passivate a trace amount of a residual metal (e.g., chromium) which has not been dissolved even by the treatment. Particularly in the production of the printed wiring board of the invention, the base metal layer is formed by sputtering plural metals, then the thus formed base metal layer is subjected to pickling treatment in order to etch the base metal layer, and then the base metal layer-forming metals which have not been removed by the pickling and have remained are passivated by the use of, for example, an oxidizing treating agent. Therefore, a printed wiring board having high insulation resistance, hardly suffering occurrence of short-circuit and having high reliability can be obtained. --

Please replace the paragraph beginning at page 36, line 20, with the following amended paragraph:

-- Then, the surface of the copper layer and the surface of the base metal layer (Ni-Cr alloy) were treated with a HCl solution as a ~~mictroetching~~ microetching solution at 40°C for 15 seconds to perform pickling. --

Please replace the paragraph beginning at page 38, line 22, with the following amended paragraph:

-- Then, the copper and the base metal layer (Ni-Cr alloy) were treated with a HCl solution as a ~~mictroetching~~ microetching solution at 40°C for 15 seconds to perform pickling. --